2SC2462

Silicon NPN Epitaxial

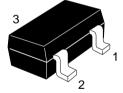
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Application

Low frequency amplifier

Outline

MPAK



- 1. Emitter
- 2. Base
- 3. Collector



2SC2462

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	50	V
Collector to emitter voltage	V _{CEO}	40	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I _c	100	mA
Emitter current	I _E	-100	mA
Collector power dissipation	P _c	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

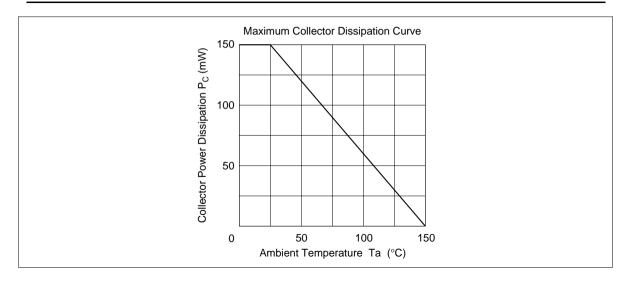
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	50	_	_	V	$I_{c} = 10 \ \mu A, \ I_{e} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	40	_	_	V	$I_{\rm C}$ = 1 mA, $R_{\rm BE}$ = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{E} = 10 \mu A, I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	0.5	μΑ	$V_{CB} = 30 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_	_	0.5	μΑ	$V_{EB} = 2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE} *1	100	_	500		$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$		_	0.2	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Base to emitter voltage	V_{BE}	_	_	0.75	V	$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$

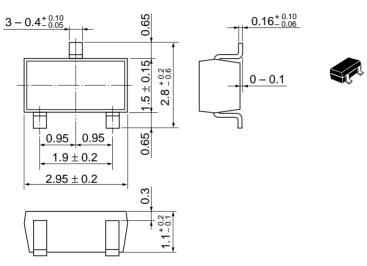
Note: 1. The 2SC2462 is grouped by h_{FE} as follows.

Grade	В	С	D
Mark	LB	LC	LD
h _{FE}	100 to 200	160 to 320	250 to 500

See characteristic curves of 2SC458 (LG).



Unit: mm



Hitachi Code	MPAK
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.011 g

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